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SIDDHARTH INSTITUTE OF ENGINEERING & TECHNOLOGY:: PUTTUR
(AUTONOMOUS)

MTECH I Year I Semester Regular Examinations July-2021

DIGITAL IC DESIGN

(VLSI)

Time: 3 hours

Max. Marks: 60

(Answer all Five Units 5 x 12 = 60 Marks)

UNIT-I

- 1 a Draw the circuit for NMOS inverter and explain its operation. L1 6M
b Draw the ideal characteristics of a CMOS inverter and compare it with the actual characteristics. L1 6M

OR

- 2 a Implement the 2-input NAND gate with CMOS logic and explain its working. L6 6M
b Discuss about the performance of dynamic CMOS inverter. L6 6M

UNIT-II

- 3 a Sketch the schematic diagram of a SRAM memory cell along with sense amplifier and data write circuitry. L1 6M
b Why low power has become an important issue in the present day VLSI circuit realization? L1 6M

OR

- 4 a Explain how read and write operations are performed in a SRAM. L2 6M
b Discuss about power consumption in CMOS gates. L6 6M

UNIT-III

- 5 a Explain in detail how do we calculate power for Bi-CMOS and on what parameters the power equation depends on? L2 8M
b List the advantages and disadvantages of Bi-CMOS. L4 4M

OR

- 6 a Compare the switching characteristics of a Bi-CMOS inverter with respect to that for static CMOS for different fan out conditions. L2 4M
b Draw the schematic diagram of different Bi-CMOS inverters. Explain its operation. L1 8M

UNIT-IV

- 7 a What is the need for design rules? Explain. L1 4M
b Write about: (i) Area capacitance (ii) Drive large capacitive load L1 6M

OR

- 8 a Explain two input NAND gate with relevant Layout example. L2 6M
b What are the CMOS based design rules? L1 6M

UNIT-V

- 9 a Explain Booth's algorithm and its modified algorithm. L2 6M
b Discuss about design approach of carry look ahead adder with neat sketch. L6 6M

OR

- 10 a Discuss about design approach of 4-bit shifter. L6 6M
b Design a 4-bit CLA adder. L6 6M

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